

US009271387B2

(12) **United States Patent**
Lee et al.

(10) **Patent No.:** **US 9,271,387 B2**
(45) **Date of Patent:** **Feb. 23, 2016**

(54) **CIRCUIT BOARD STRUCTURE
MANUFACTURING METHOD**

(71) Applicant: **BOARDTEK ELECTRONICS
CORPORATION**, Taoyuan County
(TW)

(72) Inventors: **Chien-Cheng Lee**, Taoyuan County
(TW); **Chung-Hsing Liao**, Taoyuan
County (TW)

(73) Assignee: **Boardtek Electronics Corporation**,
Taoyuan County (TW)

(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
U.S.C. 154(b) by 93 days.

(21) Appl. No.: **13/973,012**

(22) Filed: **Aug. 22, 2013**

(65) **Prior Publication Data**

US 2015/0052742 A1 Feb. 26, 2015

(51) **Int. Cl.**

H05K 3/00 (2006.01)

H05K 1/02 (2006.01)

H05K 3/42 (2006.01)

(52) **U.S. Cl.**

CPC **H05K 1/0204** (2013.01); **H05K 1/021**
(2013.01); **H05K 3/0035** (2013.01); **H05K 3/42**
(2013.01); **H05K 2201/10674** (2013.01); **H05K**
2203/025 (2013.01); **H05K 2203/0597**
(2013.01); **H05K 2203/0733** (2013.01); **Y10T**
29/49124 (2015.01)

(58) **Field of Classification Search**

CPC H05K 1/0212; Y10T 29/49124

USPC 29/829; 174/252

See application file for complete search history.

(56) **References Cited**

U.S. PATENT DOCUMENTS

5,666,722 A * 9/1997 Tamm et al. 29/847

7,235,430 B2 * 6/2007 Romano et al. 438/122

8,288,662 B2 * 10/2012 Tseng et al. 174/261

8,431,831 B2 * 4/2013 Sweeney et al. 174/262

2007/0246252 A1 * 10/2007 Buchwalter et al. 174/260

2015/0052742 A1 * 2/2015 Lee et al. 29/829

* cited by examiner

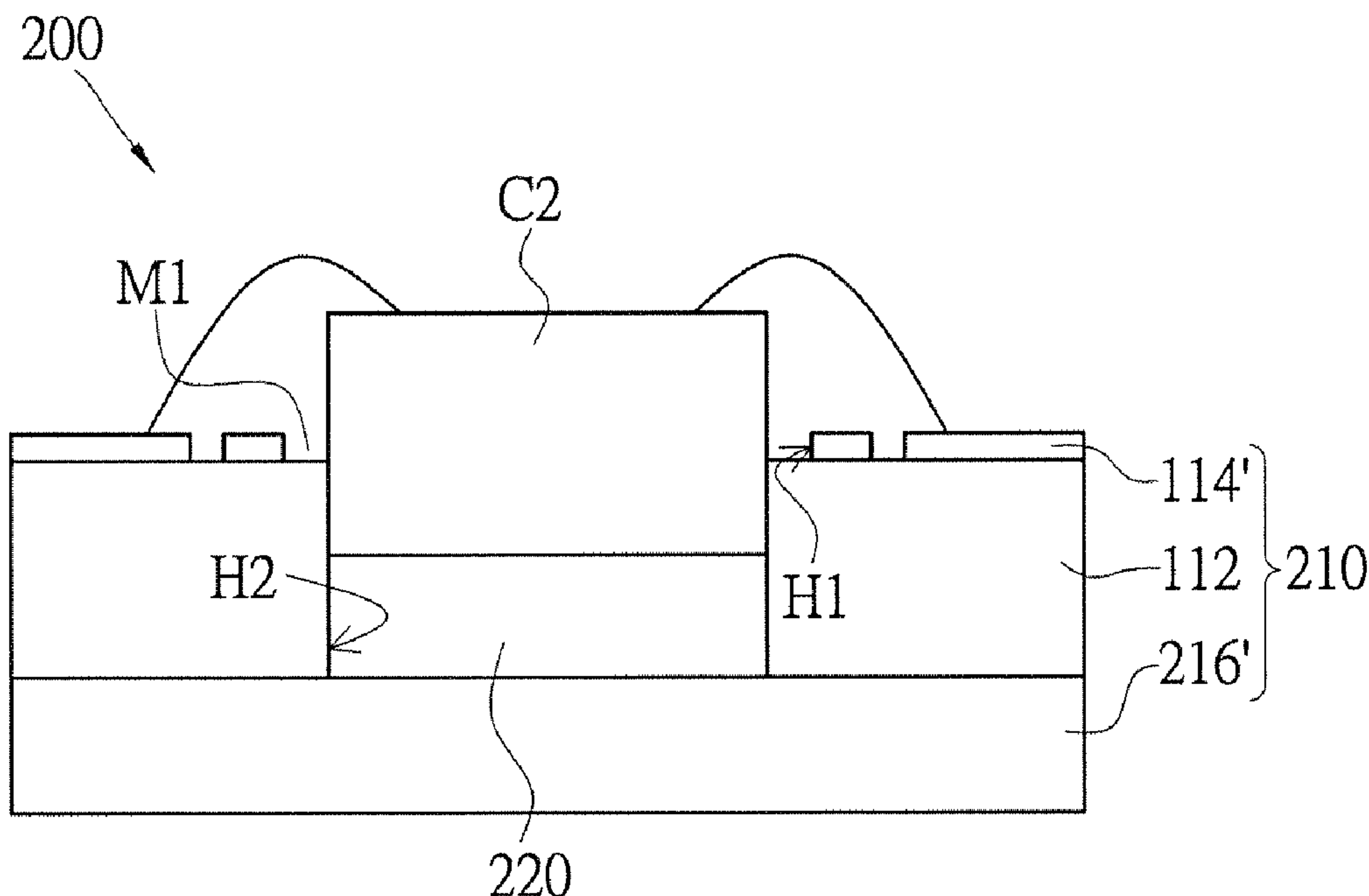
Primary Examiner — Paul D Kim

(74) *Attorney, Agent, or Firm* — Rosenberg, Klein & Lee

(57) **ABSTRACT**

A circuit board structure manufacturing method includes the following steps. A circuit substrate is provided including an insulating layer, a first metal layer, and a second metal layer. The insulating layer is disposed between the first metal layer and the second metal layer. The first metal layer has a first cavity. The insulating layer has a second cavity and a provisional region. A width of the first cavity is larger than a width of the second cavity. The provisional region is defined between a sidewall of the first metal layer defining the first cavity and another sidewall of the first metal layer defining the second cavity. A first masking layer is formed to cover the first metal layer and provisional region. The second cavity is exposed from the first masking layer. A heat-dissipating metal member is formed in the second cavity. Furthermore, the first masking layer is removed.

11 Claims, 4 Drawing Sheets



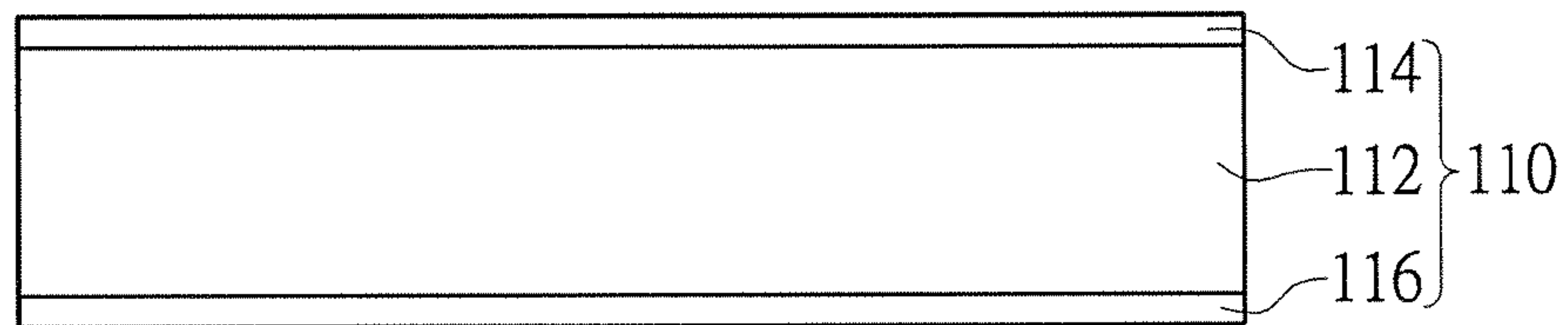


FIG. 1A

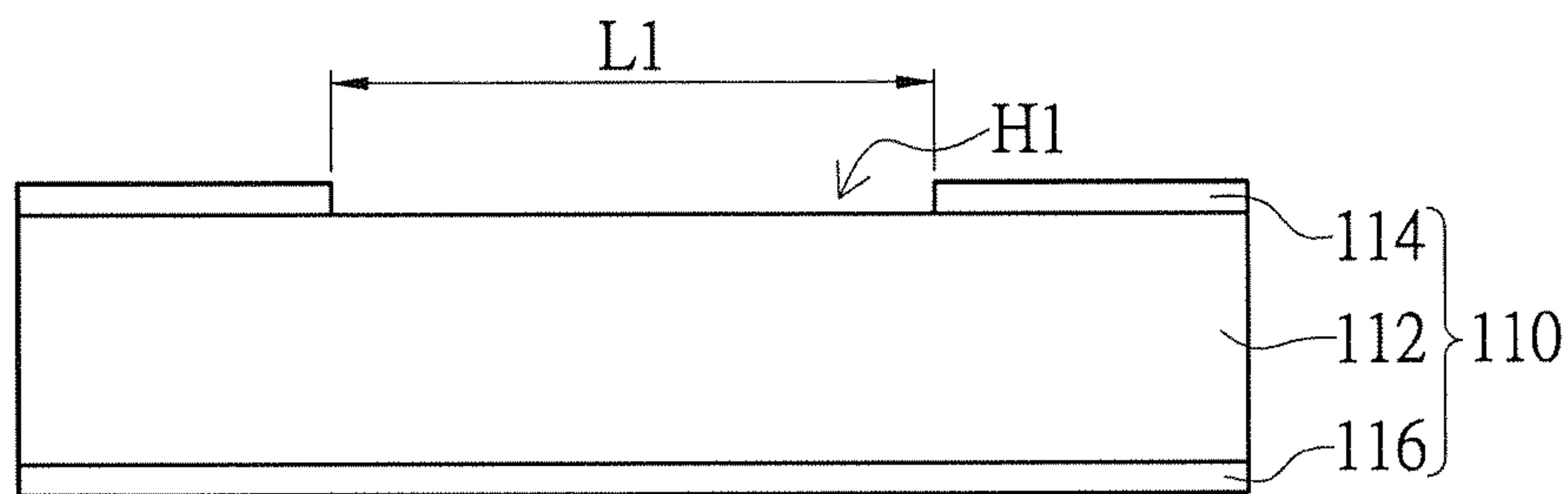


FIG. 1B

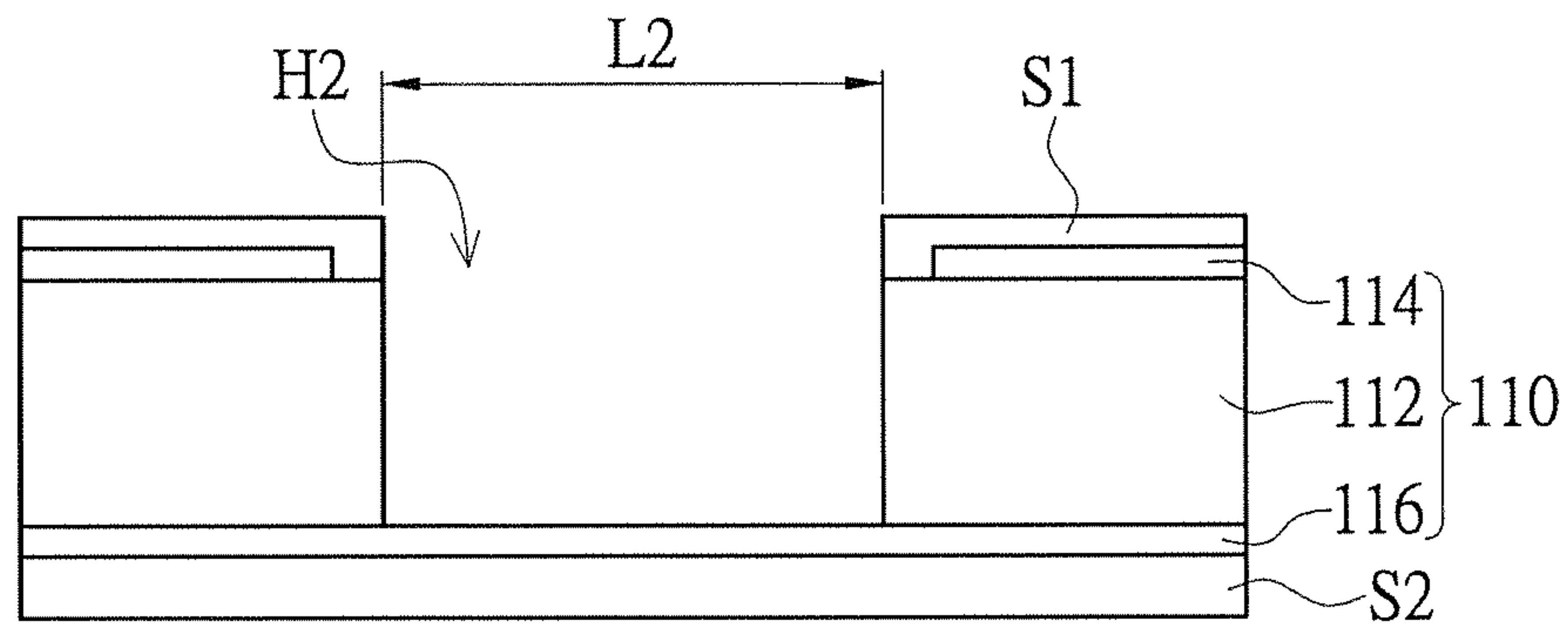


FIG.1C

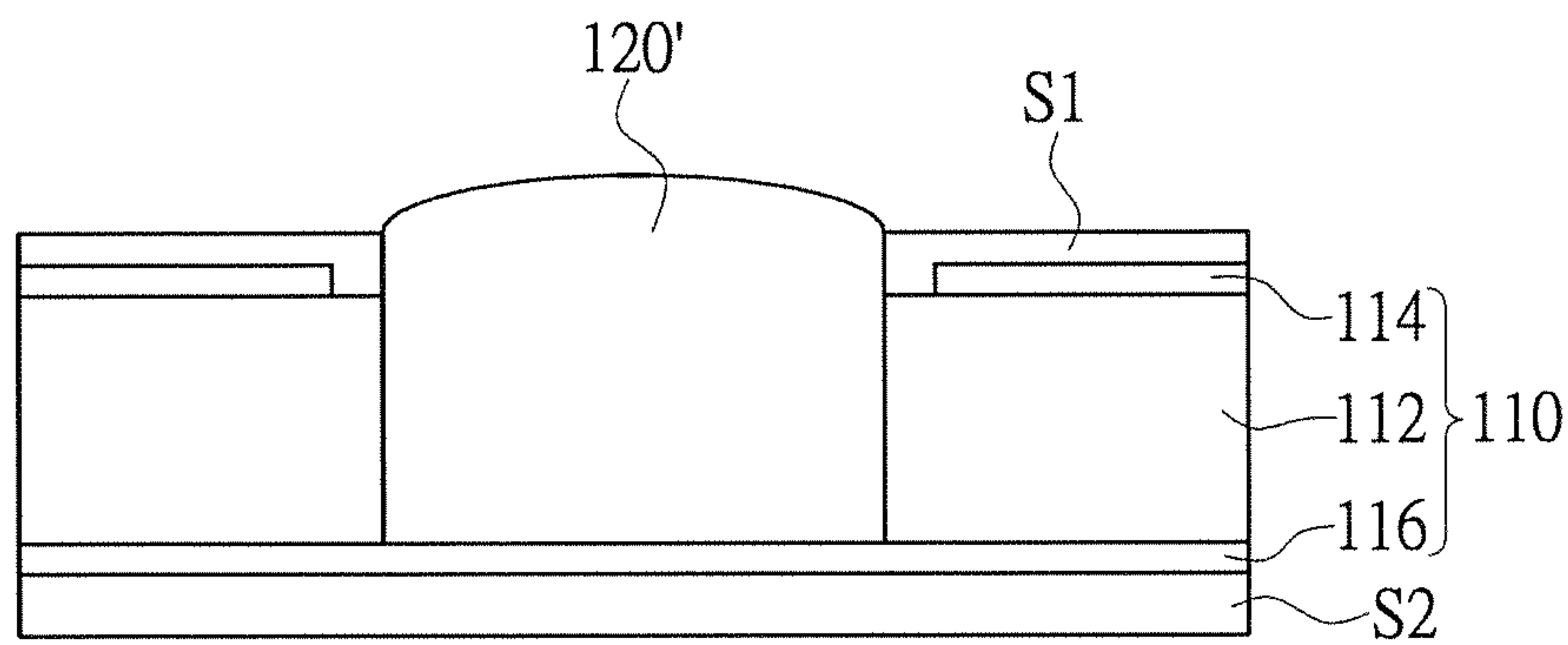


FIG.1D

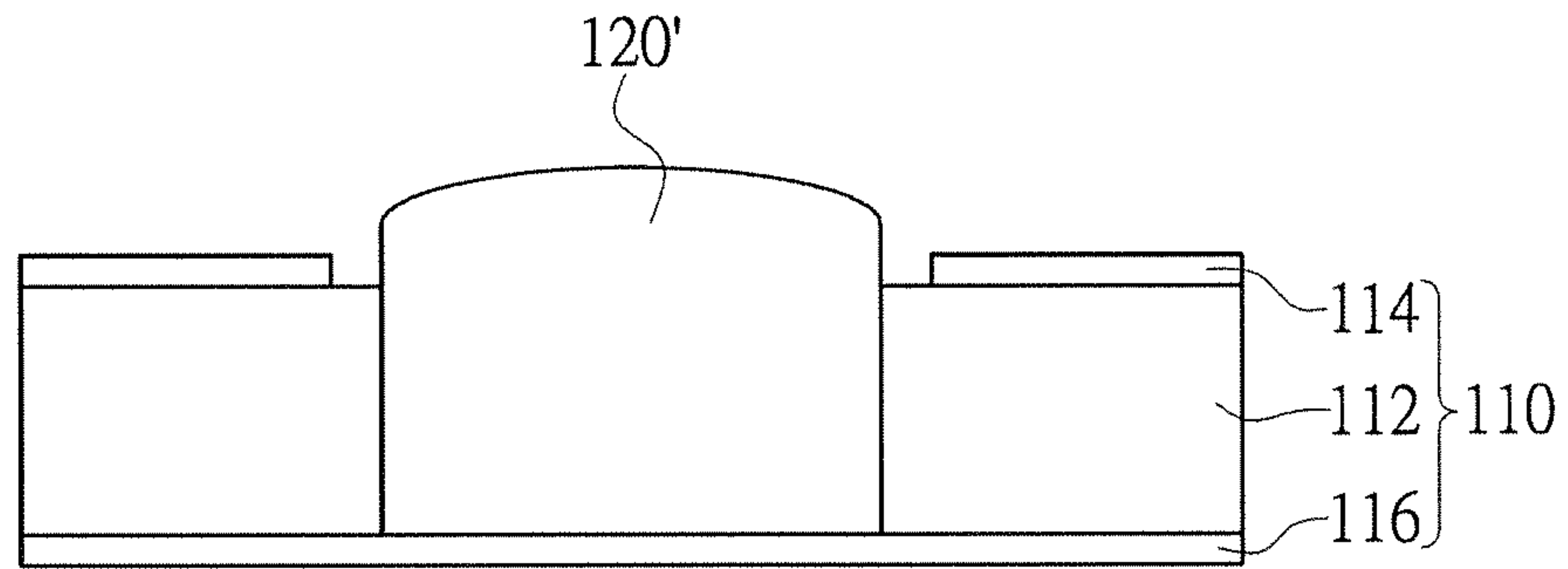


FIG. 1E

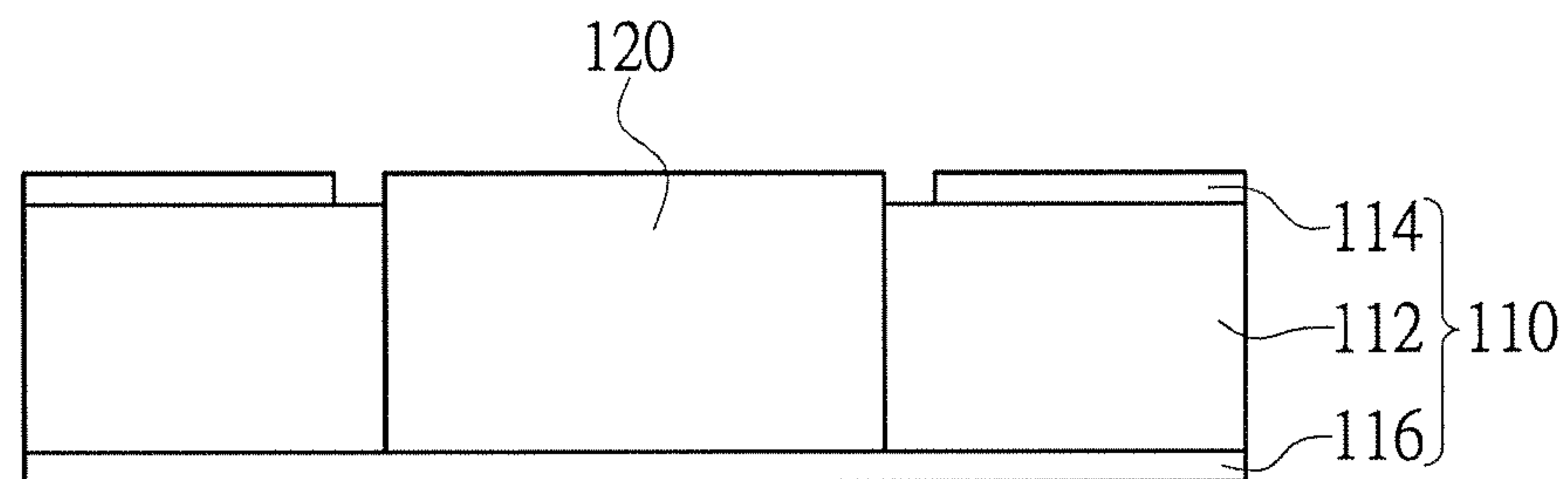


FIG. 1F

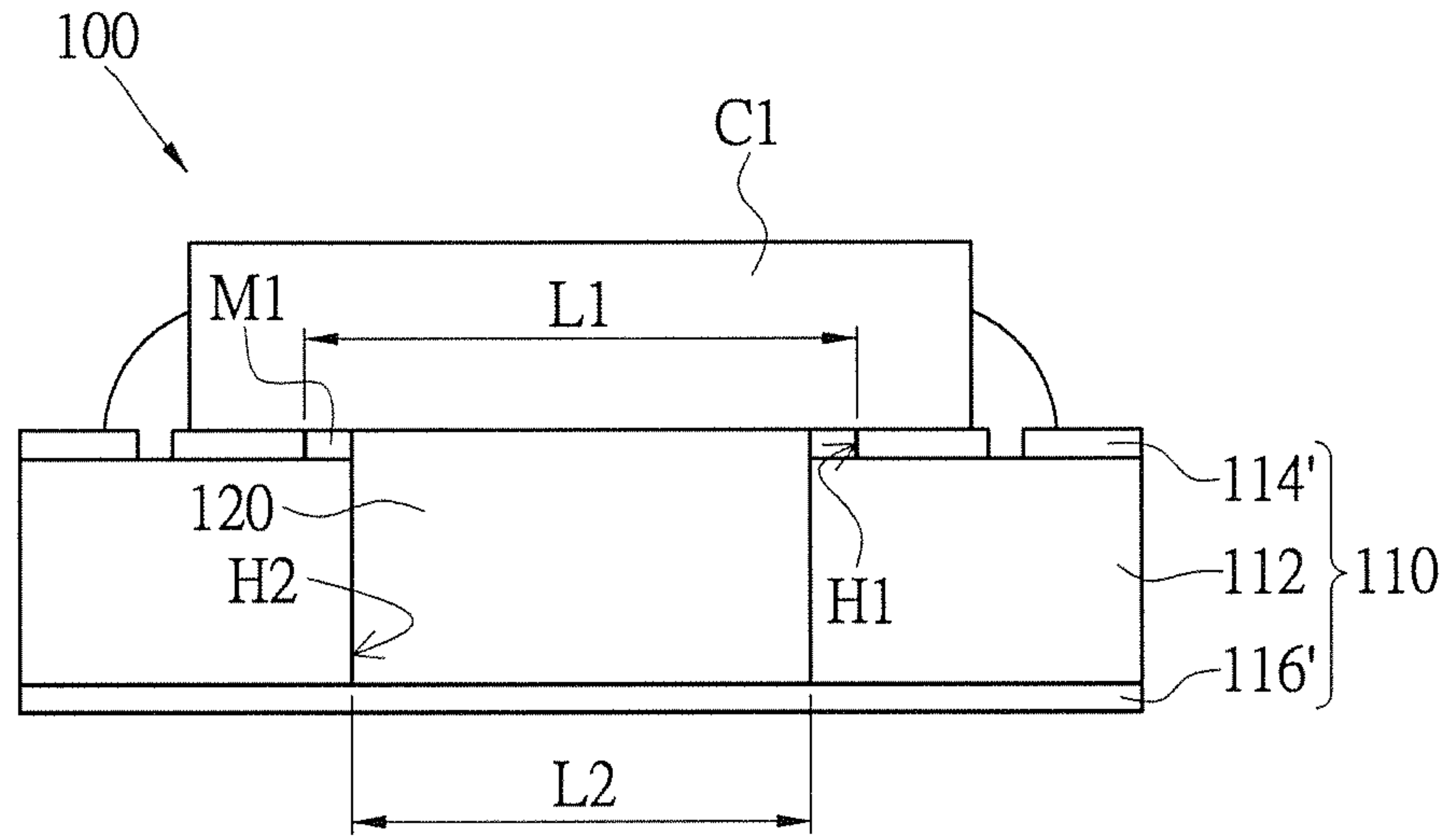


FIG. 2

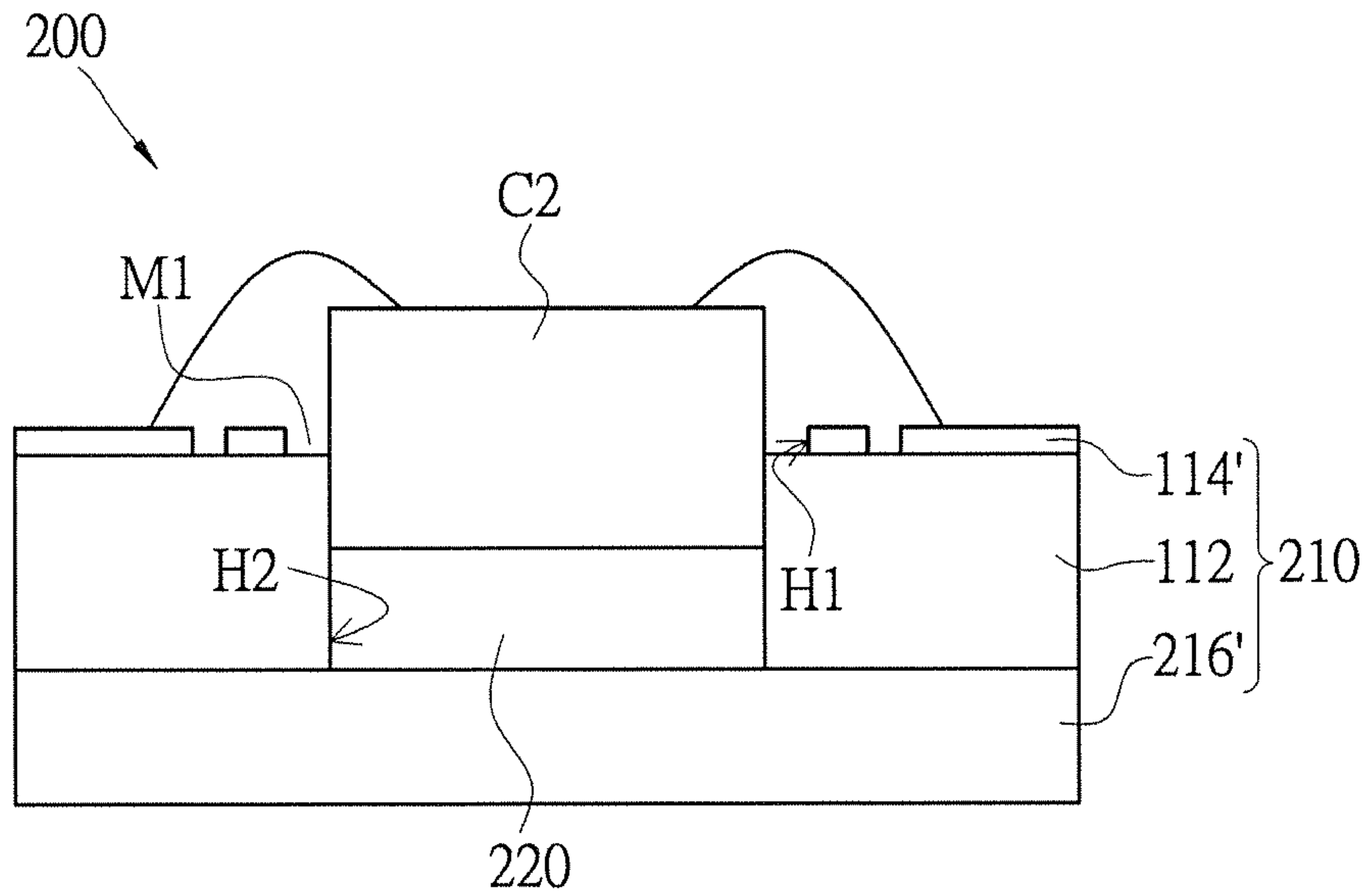


FIG. 3

1

CIRCUIT BOARD STRUCTURE
MANUFACTURING METHOD

BACKGROUND OF THE INVENTION

1. Field of the Invention

The instant disclosure relates to a circuit board structure; in particular, to a manufacturing method of the circuit board structure.

2. Description of Related Art

Under the trend of miniaturization, the overall module packaging of the common electronic products, such as mobile phones or notebook computers, becomes denser. Thus, functionalities of the electronic products are becoming more versatile, rendering larger power consumption which leads to enormous amount of heat generated and the overall temperature to increase. In order to lower the temperature due to overheating, the circuit board tends to be designed with copper (e.g. copper rod or column) thereon as a way to dissipate heat for the electronic components.

Typically, in the conventional method of electroplating a heat dissipating copper column, a two-sided copper-clad laminate of the circuit board is usually drilled through, and the sidewalls of the drilled cobalt holes are electroplated with a layer of copper. However, since copper ions tend to aggregate near the edges of the traces, sidewalls of openings or wall junctions between sidewalls of openings and heat dissipating copper columns, excess aggregation of copper ions tends to form copper lumps at the wall junctions.

To address the above issues, the inventor strives via associated experience and research to present the instant disclosure, which can effectively improve the limitation described above.

SUMMARY OF THE INVENTION

The object of the instant disclosure is to provide a manufacturing method for a circuit board structure which has heat-dissipating metal columns that can facilitate heat dissipation of the circuit board structure.

In order to achieve the aforementioned objects, according to an embodiment of the instant disclosure, a circuit board structure is provided which includes a circuit substrate and at least one heat-dissipating metal member. The circuit substrate includes an insulating layer, a first metal layer, and a second metal layer. The insulating layer is disposed between the first metal layer and the second metal layer. The first metal layer has portions defining a first cavity. The insulating layer has portions defining a second cavity. The second cavity is exposed through the second metal layer. The first cavity has a width larger than a width of the second cavity and the heat-dissipating metal member is formed in the second cavity.

In summary, the embodiment of the instant disclosure provides a manufacturing method for a circuit board structure. The first cavity has a width larger than a width of the second cavity. The provisional region is defined by a sidewall of the first metal layer defining the first cavity and a sidewall of the insulating layer defining the second cavity. The first masking layer is formed to cover the first metal layer and the provisional region such that metal ions are less susceptible to attach near edges of the second cavity during the formation of the heat-dissipating metal member via electroplating. As a result, the heat-dissipating metal member is fully formed via electroplating.

In order to further understand the instant disclosure, the following embodiments and illustrations are provided. However, the detailed description and drawings are merely illus-

2

trative of the disclosure, rather than limiting the scope being defined by the appended claims and equivalents thereof.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1A to 1F are schematic diagrams illustrating the steps of forming a circuit board structure in accordance with a circuit board structure manufacturing method of the instant disclosure;

FIG. 2 is a schematic diagram of the circuit board structure manufacturing method in accordance with a first embodiment of the instant disclosure; and

FIG. 3 is a schematic diagram of the circuit board structure manufacturing method in accordance with a second embodiment of the instant disclosure.

DETAILED DESCRIPTION OF THE PREFERRED
EMBODIMENTS

FIG. 1A to 1F are schematic diagrams illustrating the steps of forming a circuit board structure in accordance with a circuit board structure manufacturing method of the instant disclosure. Please refer to FIGS. 1A to 1F.

Please refer to FIG. 1A. Firstly, a circuit substrate **110**, which includes an insulating layer **112**, a first metal layer **114** and a second metal layer **116**, is provided. The insulating layer **112** is sandwiched between the first metal layer **114** and the second metal layer **116**. In the instant embodiment, the circuit substrate **110** is a two-sided metal-clad laminate. The first metal layer **114** and second metal layer **116** are disposed on opposite sides of the insulating layer **112**. Generally, the first, second metal layers **114**, **116** are made of metal foils (or thin films) such as copper foils. However, the circuit substrate **110** can also be a ready-made multi-layered circuit board, and is not limited hereto.

Please refer to FIG. 1B. A pattern is developed on the first metal layer **114** such that a first cavity **H1** is formed thereon. Specifically, the first cavity **H1** is formed by removing portions of the first metal layer **114** via photolithography etching. As a result, portions of the insulating layer **112** are exposed via the first cavity **H1**. In addition, the first cavity **H1** has a width **L1**.

Please refer to FIG. 1C. A pattern is developed on the insulating layer to form the second cavity passing through the second metal layer. Specifically, the second cavity **H2** is formed by removing materials from the insulating layer **112** through the first cavity **H1**. Notably, the second metal layer **116** is exposed via the second cavity **H2**. The width **L1** of the first cavity **H1** is larger than a width **L2** of the second cavity **H2**. The second cavity **H2** can be formed by laser drilling or milling. Specifically, the second cavity **H2** is formed by downwardly eroding the insulating layer **112** through the first cavity **H1**, as if a cavity extending from the first cavity **H1**, via laser ablation. Portions of the insulating layer **112** which are exposed through the first cavity **H1** can be milled to form the second cavity **H2**. Alternatively, the second cavity **H2** can also be first milled to remove portions of the insulating layer **112**, then further removing other portions of the insulating layer **112** via laser ablation. Successively, remaining insulating layer **112** is removed, which are left on a surface of the second metal layer **116**, via chemicals.

The insulating layer **112** has a provisional region **M1** which is defined by a sidewall of the first metal layer **114** defining the first cavity **H1** and a sidewall of the insulating layer **112** defining the second cavity **H2**. Specifically, the provisional region **M1** is defined as the spaced apart region above the insulating layer **112**, and between the sidewall of the first

metal layer **114** defining the first cavity **H1** and the sidewall of the insulating layer **112** defining the second cavity **H2**. In other words, the first metal layer **114** does not completely covers the insulating layer **112**.

A first masking layer **S1** is formed to cover the first metal layer **114** and the provisional region **M1**, and a second masking layer **S2** is formed to cover the second metal layer **116**. Specifically, the first masking layer **S1** and the second masking layer **S2** can be anti-etching dry film, photoresist or other insulating materials. The first masking layer **S1** covers the first metal layer **114** and the provisional region **M1**, and the first masking layer **S1** exposes the second cavity **H2**. The second masking layer **S2** covers the outer surface of the second metal layer **116**. Notably, the first masking layer **S1** and the second masking layer **S2** expose only the second metal layer **116** via the second cavity **H2**. The instant disclosure does not limit the sequence of the procedures or steps to simultaneously or sequentially forming the first, second masking layers **S1**, **S2**, and the first, second cavities **H1**, **H2**.

Moreover, in another embodiment of the instant disclosure, the circuit board structure **100** manufacturing method can also include forming the first masking layer **S1** to cover the first metal layer **114** and the first cavity **H1** before the second cavity **H2** is formed by extending the first cavity **H1** through the insulating layer **112**. Moreover, the second masking layer **S2** is formed to cover the second metal layer **116**. Specifically, a pattern is developed on the first metal layer **114**, after the first metal layer **114** is formed with a first cavity **H1**, the first masking layer **S1** is formed to cover the first metal layer **114** and the first cavity **H1** while exposing the insulating layer **112**. The second masking layer **S2** is formed on a surface of the second metal layer **116**. Then, the second cavity **H2** is formed through the first masking layer **S1** and the insulating layer **112**.

Furthermore, in another embodiment of the instant disclosure, the circuit substrate **110** can also be formed by the build up process. Specifically, first providing the insulating layer **112**. The second cavity **H2** is formed on the insulating layer **112**. Thereafter, two opposite sides of the insulating layer **112** are respectively covered by the first metal layer **114** and the second metal layer **116**, in which the first metal layer **114** already has the first cavity **H1** formed thereon. Namely, the first metal layer **114** has not yet covered the provisional region **M1**. After high temperature lamination, the circuit substrate **110** is formed.

Please refer to FIG. **1D**. The first masking layer **S2** is used as a mask. A heat-dissipating metal member **120'** is formed in the second cavity **H2** via electroplating. Specifically, copper is plated to fill in the second cavity **H2** via electroplating in order to form the solid heat-dissipating metal member **120'**. Generally in forming the heat-dissipating metal member via conventional electroplating methods, metal ions (e.g. copper ions) are susceptible to aggregate near edges of metal layers, for example, near edges of the traces or near edges of openings of the metal layers. In turn excess metal (copper nodule) is susceptible to form near edges of the metal layers, and as a result, product yield is decreased.

However, since the first masking layer **S2** covers the first metal layer **114** and the provisional region **M1**, edges of the second cavity **H2** is less likely to aggregate metal ions which in turn forms metal nodules during the formation of the heat-dissipating metal member **120'** via electroplating. Thus, the heat-dissipating metal member **120'** can be fully formed. Moreover, the second masking layer **S2** covers a surface of the second metal layer **116** to prevent metal ions from attaching onto the second metal layer **116**.

Please refer to FIG. **1E**. The first and second masking layers **S1**, **S2** are removed. Since the first, second masking layers **S1**, **S2** can be anti-etching dry film or photoresist, both layers **S1**, **S1** can be removed by an aqueous solution of sodium hydroxide.

Please further refer to FIG. **1F**. In order to facilitate installing of electronic components **C1** onto a leveled top portion of the heat-dissipating metal member **120'**, the circuit board structure **100** manufacturing method also includes abrasively treating. Specifically, the top portion of the heat-dissipating metal member **120'** is abrasively treated via belt grinding machines to form a leveled top portion of heat-dissipating metal member **120'**. As a result, electronic components **C1** can be easily installed onto the top portion of the heat-dissipating metal member **120'**. Notably, in order to accommodate various sizes and designs of electronic components **C1**, the heat-dissipating metal member **120'** may have various heights. In other words, the top portion of the heat-dissipating metal member **120'** can be higher or lower than a top surface of the first metal layer **114**. In the instant embodiment, the top portion of the heat-dissipating metal member **120'** is abrasively treated to be substantially leveled with the top surface of the first metal layer **114**. However, in a second embodiment, the top portion of the heat-dissipating metal member **120'** can be abrasively treated to be lower than the first metal layer **114**, which is denoted as the heat-dissipating metal member **220**.

Furthermore, traces can be etched thereafter. Surfaces of the first metal layer **114** and the second metal layer **116** are etched to respectively form a first circuit layer **114'** and a second circuit layer **116'**. However, the etching process is not limited to the examples provided herein.

Thereafter, the electronic components can be installed via wired bonding, flip clip or other methods to electrically connect the first metal layer **114** and be disposed onto the heat-dissipating metal member **120**. In addition, the heat-dissipating metal member **120** can dissipate heat to the environment such that normal operations of the electronic components are not affected by overheating.

Please refer again to FIG. **1F** as a schematic diagram of the circuit board structure in accordance with the instant embodiment of the instant disclosure. The circuit board structure **100** includes the circuit substrate **110** and the heat-dissipating structure **120**. The circuit substrate **110** includes the first metal layer **114**, the second metal layer **116**, and the insulating layer **112** which is sandwiched between the first and second metal layers **114**, **116**. The first metal layer **114** has the first cavity **H1**, and the insulating layer **112** has the second cavity **H2**. The heat-dissipating metal member **120** is disposed in the second cavity **H2**.

The circuit substrate **110** serves as a carrier of various electronic components. In general, the insulating layer **112** of the circuit substrate **110** has the first, second metal layers **112**, **114** installed thereon, and the first, second metal layers **112**, **114** includes bonding pads and traces. In practice, the first, second metal layers **112**, **114** may have various configurations depending on the required electrical connections in which the product demands.

In the instant embodiment, the circuit substrate **110** is a two-sided circuit board structure. The insulating layer **112**, and the first, second metal layers **112**, **114** cooperatively form the circuit substrate **110**. However, in another embodiment, the circuit substrate **110** can be a multi-layer circuit board structure. The circuit substrate **110** may include two or more insulating layers **112** which are located between the first and second metal layers **114**, **116**. Notably, the circuit substrate

5

110 can also be a two-sided circuit board structure or a multi-layer circuit board structure, but is not limited herein.

The insulating layer 112 is positioned between the first and second metal layers 114, 116, and the first metal layer 114 has the first cavity H1, the insulating layer 112 has the second cavity H2. Notably, the second cavity H2 is formed by extending the first cavity H1 through the insulating layer 112. In other words, the first and second cavities H1, H2 are concentric. The first cavity width L1 is larger than the second cavity width L2 such that the insulating layer 112 is exposed through the first cavity H1, and the second metal layer 116 is exposed through the second cavity H2.

Notably, the insulating layer 112 is generally formed with pre-impregnated (pre-preg) materials. The pre-preg layer can be categorized as glass fiber, carbon fiber, or epoxy resin type of pre-preg according to the type of enhancing materials. However, the insulating layer 112 can be made of flexible substrate materials. In other words, the insulating layer 112 is substantially made of polyester (PET) or polyimide (PI) and excludes glass fibers, carbon fibers, etc. However, the materials of the insulating layer 112 are not limited herein.

The heat-dissipating metal member 120 is installed in the second cavity H2, and connected to the second metal layer 116 so that electronic components can be installed on the heat-dissipating metal member 120. The heat-dissipating metal member 120 dissipates heat to the environment such that normal operations of the electronic components are not affected by overheating.

Notably, in order to accommodate various sizes and designs of electronic components, the heat-dissipating metal member 120 may have various heights. In other words, the top portion of the heat-dissipating metal member 120 can be higher than, lower than, or leveled with a top surface of the first metal layer 114.

FIG. 2 is a schematic diagram of the circuit board structure manufacturing method in accordance with a first embodiment of the instant disclosure. Please refer to FIG. 2. In the instant embodiment, a top surface of the heat-dissipating metal member 120 is substantially leveled with a top surface of the first metal layer 114, and the electronic component C1 is installed on the heat-dissipating metal member 120. Accordingly, heat generated by electronic components C1 can be transferred to the environment via the heat-dissipating metal member 120. Notably, the electronic component C1 can be electrically connected to the first circuit layer 114' via wire bonding, flip chip or other methods. The first and second circuit layers 114', 116' can be respectively formed by etching the first and second metal layers 114, 116. In addition, in another embodiment, the first and second metal layers 114, 116 can also respectively be the first and second circuit layers 114', 116'. The electronic component C1 is installed on and thermally coupled to the heat-dissipating metal member 120.

FIG. 3 is a schematic diagram of the circuit board structure manufacturing method in accordance with a second embodiment of the instant disclosure. The structure and the effect of the circuit board structure 200 of the second embodiment is substantially the same as the circuit board structure 100 of the first embodiment. For example, the circuit board structures 200, 100 both include insulating layer. The following discloses the differences between the two circuit board structures 200, 100.

Please refer to FIG. 3, the circuit board structure 200 of the second embodiment includes the first circuit layer 114', the second circuit layer 216', and the insulating layer 112 which is sandwiched between the first circuit layer 114' and the second circuit layer 216'. The first circuit layer 114' has the first cavity H1, and insulating layer 112 has the second cavity

6

H2. The heat-dissipating metal member 220 is installed in the second cavity H2. The electronic component C2 is disposed in the second cavity H2 and above the heat-dissipating metal member 220. The electronic component C2 and the first circuit layer 114' is electrically connected and thermally coupled to the heat-dissipating metal member 220. The first circuit layer 114' is formed by etching the first metal layer 114. Moreover, in another embodiment, the first metal layer 114 and the second metal layer 216 can be the first circuit layer 114', and the second circuit layer 216'. Notably, in order to increase current carrying capacity of the circuit board structure 200, the second metal layer 216 is a thick copper layer. However, the thickness of the second metal layer 216 is not limited herein.

In the instant embodiment, a top surface of the heat-dissipating metal member 220 is substantially leveled with a top surface of the first metal layer 114 but is not limited herein. The electronic component C2 is installed on the heat-dissipating metal member 220. Accordingly, heat generated by the electronic components C2 can be transferred to the environment via the heat-dissipating metal member 220.

In summary, the instant embodiment provides circuit board structures and the manufacturing method of the same. The first cavity width of the circuit board structure is larger than the second cavity width. The provisional region is defined by a sidewall of the first metal layer defining the first cavity and a sidewall of the insulating layer defining the second cavity. The first masking layer covers the first metal layer and the provisional region such that metal ions are less susceptible to form metal nodules near edges of the second cavity during the formation of the heat-dissipating metal member via electroplating. As a result, the heat-dissipating metal member is fully formed via electroplating.

The figures and descriptions supra set forth illustrated the preferred embodiments of the instant disclosure; however, the characteristics of the instant disclosure are by no means restricted thereto. All changes, alternations, combinations or modifications conveniently considered by those skilled in the art are deemed to be encompassed within the scope of the instant disclosure delineated by the following claims.

What is claimed is:

1. A circuit board structure manufacturing method comprising the steps of:
 - providing a circuit board, the circuit board comprising:
 - an insulating layer;
 - a first metal layer; and
 - a second metal layer;
 wherein the insulating layer is disposed between the first metal layer and the second metal layer, the first metal layer has portions defining a first cavity, the insulating layer has portions defining a second cavity and an empty region, the first cavity has a width larger than a width of the second cavity, and the empty region is defined by a sidewall of the first metal layer defining the first cavity and a sidewall of the insulating layer defining the second cavity;
 - applying a first masking layer covering the first metal layer and the empty region, wherein the first masking layer exposes the second cavity;
 - after applying the first masking layer, electroplating a metal member in the second cavity; and
 - after electroplating the metal member, removing the first masking layer;
- wherein the first masking layer is formed after the second cavity is formed and the first masking layer covers the first metal layer and the empty region of the first cavity.

7

2. The circuit board structure manufacturing method as recited in claim 1, wherein in the step of providing a circuit board, the first and second cavities are formed by the steps comprising:

developing a pattern on the first metal layer to form the first cavity; and

forming the second cavity through the insulating layer and exposing the second metal layer.

3. The circuit board structure manufacturing method as recited in claim 2, wherein the step of developing a pattern on the first metal layer comprises the step of:

laser-ablating the first metal layer to form the first cavity thereon.

4. The circuit board structure manufacturing method as recited in claim 1 further comprising the step of:

abrasively treating the heat-dissipating metal member to flatten a top portion thereof.

5. The circuit board structure manufacturing method as recited in claim 4, wherein the top portion of the heat-dissipating metal member and the first metal layer are leveled.

6. The circuit board structure manufacturing method as recited in claim 4, wherein the top portion of the heat-dissipating metal member is lower in height than the insulating layer.

8

7. The circuit board structure manufacturing method as recited in claim 1, wherein the first masking layer is formed after the second cavity is formed and the first masking layer covers the first metal layer and the first cavity.

8. The circuit board structure manufacturing method as recited in claim 1 wherein the first masking layer is formed before the second cavity is formed and the first masking layer covers the first metal layer and the first cavity.

9. The circuit board structure manufacturing method as recited in claim 1 further comprising the step of:

disposing an electronic component on and coupled to the heat-dissipating metal member, wherein the electronic component is electrically connected to the first metal layer.

10. The circuit board structure manufacturing method as recited in claim 1 further comprising the step of:

forming a second masking layer covering the second metal layer.

11. The circuit board structure manufacturing method as recited in claim 1, wherein the second cavity is formed by laser-ablating the insulating layer.

* * * * *

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 9,271,387 B2
APPLICATION NO. : 13/973012
DATED : February 23, 2016
INVENTOR(S) : Chien-Cheng Lee and Chung-Hsing Liao

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

IN THE TITLE PAGE:

ITEM [54] DELETE THE TITLE "CIRCUIT BOARD STRUCTURE MANUFACTURING METHOD" AND INSERT --CIRCUIT BOARD AND MANUFACTURING METHOD THEREOF--

Signed and Sealed this
Seventeenth Day of May, 2016



Michelle K. Lee
Director of the United States Patent and Trademark Office